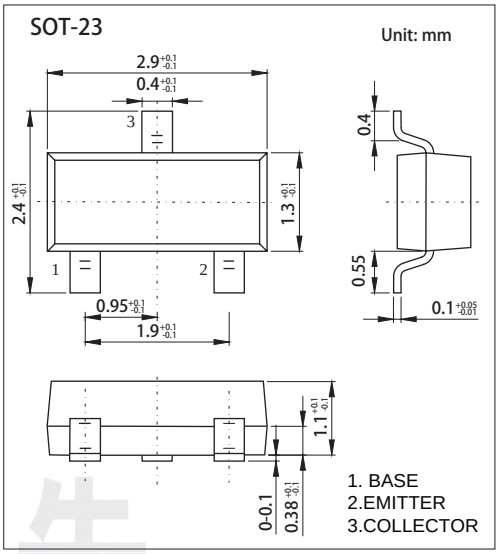
PNP Transistors

S9015



■ Features

- Collector current: Ic=-0.1A
- Complementary to S9014

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CBO}	I_C= -100 μA， I_E=0	-50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -0.1 mA， I_B=0	-45			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μA， I_C=0	-5			
Collector cut-off current	I_{CBO}	V_{CB}= -50 V , I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100 mA, I_B= -10mA			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-100 mA, I_B= -10mA			-1	
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -1mA	200		1000	
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA,f=30MHz	150			MHz

■ Classification of hFE

Rank	L	H
Range	200-450	450-1000
Marking	M6	

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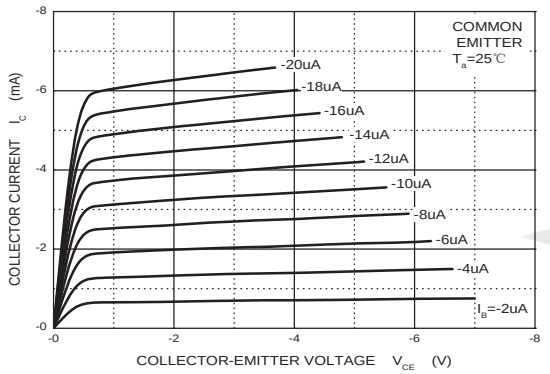
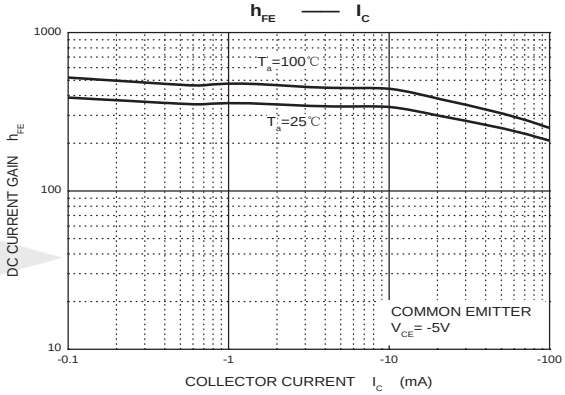
■ Typical Characterisitics

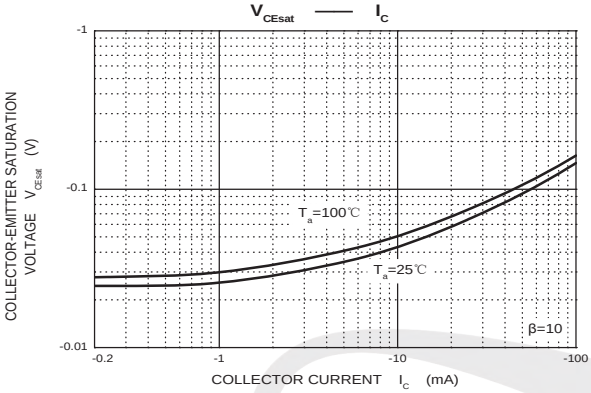
Static Characteristic



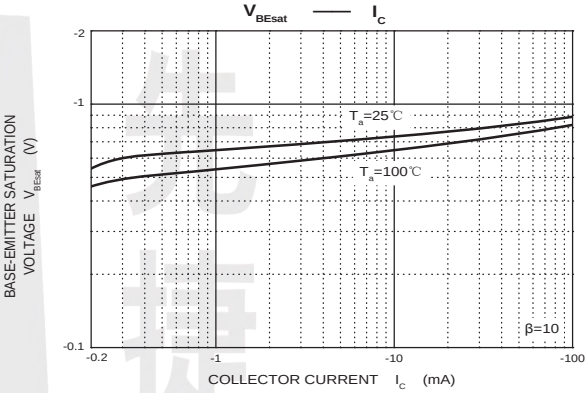
h_{FE} —— I_C



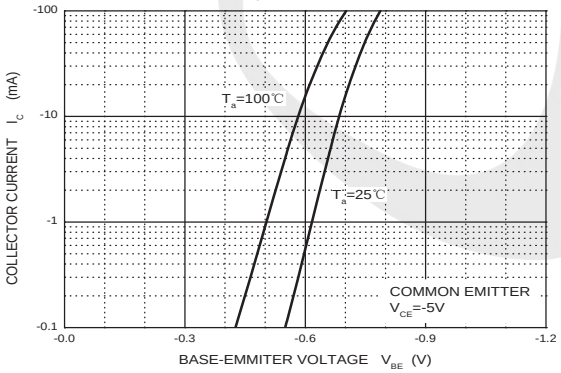
V_{CEsat} —— I_C



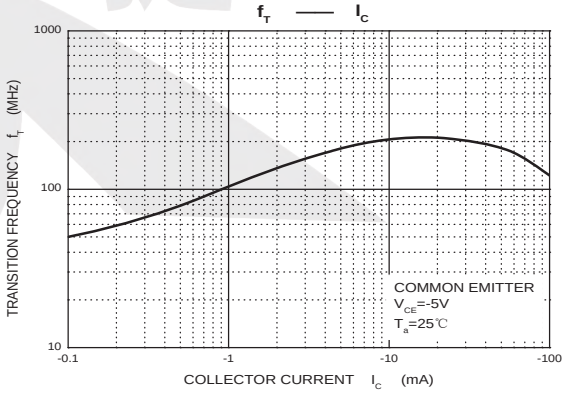
V_{BEsat} —— I_C



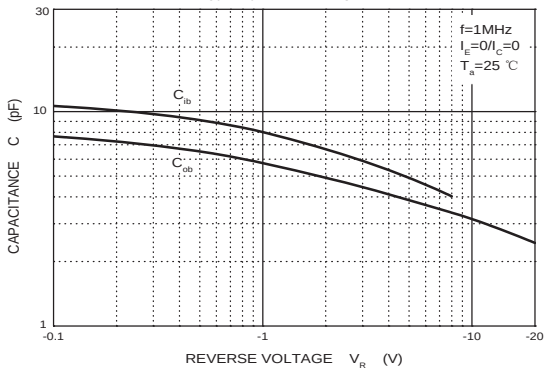
I_C —— V_{BE}



f_T —— I_C



C_{ob} / C_{ib} —— V_{CB} / V_{EB}



P_C —— T_a